

STD10P6F6, STF10P6F6, STP10P6F6

P-channel -60 V, 0.13 Ω typ., -10 A STripFET™ F6 Power MOSFETs in DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet - production data

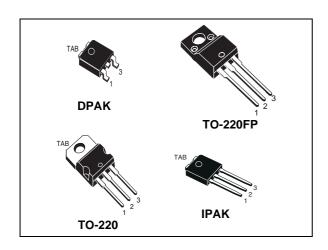
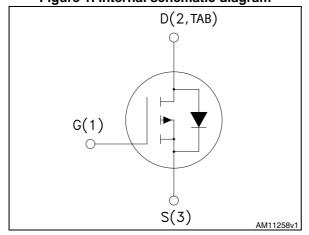


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max	I _D
STD10P6F6			
STF10P6F6	-60 V	0.16 Ω	-10 A
STP10P6F6	-00 V	0.10 12	-10 A
STU10P6F6			

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- · Low gate drive power loss

Applications

· Switching applications

Description

These devices are P-channel Power MOSFETs developed using the STripFETTM F6 technology, with a new trench gate structure. The resulting Power MOSFETs exhibit very low $R_{DS(on)}$ in all packages.

Table 1. Device summary

Order codes	Marking	Package	Packing
STD10P6F6		DPAK	Tape and reel
STF10P6F6	400000	TO-220FP	
STP10P6F6	10P6F6	TO-220	Tube
STU10P6F6		IPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	DPAK IPAK	TO-220FP	TO-220	Unit
V _{DS}	Drain-source voltage		-60		V
V _{GS}	Gate-source voltage		± 20		V
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25 °C		-10		Α
I _D	Drain current (continuous) at T _C = 100 °C		-7.2		Α
I _{DM} ⁽²⁾	Drain current (pulsed)	-40		Α	
P _{TOT}	Total dissipation at T _C = 25 °C	35	20	30	W
E _{AS}	Single pulse avalanche energy (starting T _J =25 °C, I _D =-3 A, V _{DD} =40 V)		80		mJ
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	2500			V
V _{DG}	Drain-gate voltage (V _{GS} = 0)		-20		V
T _{stg}	T _{stg} Storage temperature		-55 to 175		
T _j	Max. operating junction temperature		175		°C

^{1.} Limited by package

Table 3. Thermal data

Symbol	Parameter		Unit				
Symbol	r ai ailletei	DPAK IPAK		TO-220FP	TO-220		
R _{thj-case}	Thermal resistance junction-case max	4.29		7.5	5	°C/W	
R _{thj-amb}	Thermal resistance junction-ambient max		100	62.5	62.5	°C/W	
R _{thj-pcb}	Thermal resistance junction-pcb max ⁽¹⁾	50				°C/W	

^{1.} When mounted on 1 inch² FR-4, 2 Oz copper board

^{2.} Pulse width limited by safe operating area

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified).

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown Voltage	I _D = -250 μA, V _{GS} = 0 V	-60			V
1	Zero gate voltage drain	V _{DS} = -60 V			-1	μΑ
I _{DSS}	current (V _{GS} = 0)	V _{DS} = -60 V, Tc = 125 °C			-10	μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2		-4	V
R _{DS(on)}	Static drain-source on- resistance	$V_{GS} = -10 \text{ V}, I_D = -5 \text{ A}$		0.13	0.16	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance		-	340	-	pF
C _{oss}	Output capacitance	$V_{DS} = -48 \text{ V, f=1 MHz,}$	1	40	ı	pF
C _{rss}	Reverse transfer capacitance	V _{GS} = 0 V	-	20	-	pF
Qg	Total gate charge	V _{DD} = -30 V, I _D = -10 A	ı	6.4	ı	nC
Q_{gs}	Gate-source charge	V _{GS} = -10 V	-	1.7	-	nC
Q_{gd}	Gate-drain charge	(see Figure 16)	-	1.7	-	nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time		-	64	-	ns
t _r	Rise time	$V_{DD} = -48 \text{ V}, I_{D} = -5 \text{ A},$ $R_{G} = 4.7 \Omega, V_{GS} = -10 \text{ V}$	-	5.3	-	ns
t _{d(off)}	Turn-off delay time	(see Figure 15)	-	14	-	ns
t _f	Fall time		-	3.7	-	ns



Table 7. Source drain diode

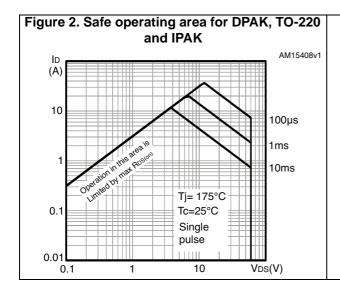
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current		-		-10	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		-40	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = -5 A, V _{GS} = 0 V	-		-1.1	٧
t _{rr}	Reverse recovery time	I _{SD} = -10 A,	-	20		ns
Q _{rr}	Reverse recovery charge	di/dt = -100 A/μs, V _{DD} = -48 V	-	17.8		nC
I _{RRM}	Reverse recovery current	(see Figure 17)	-	-1.8		А

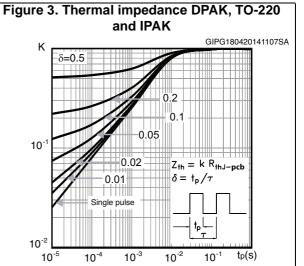
^{1.} Pulse width limited by safe operating area.

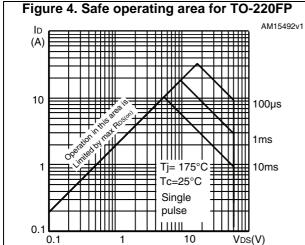
^{2.} Pulsed: pulse duration = $300 \mu s$, duty cycle 1.5%

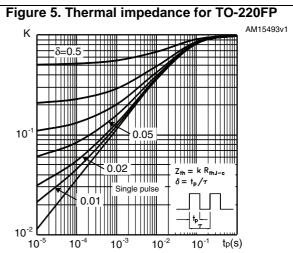
2.1 Electrical characteristics (curves)

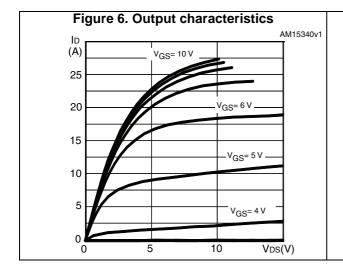
Note: For the P-channel Power MOSFET, current and voltage polarities are reversed.











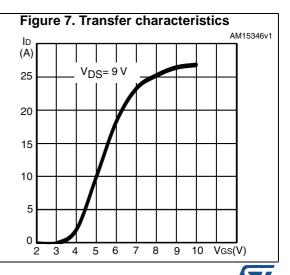
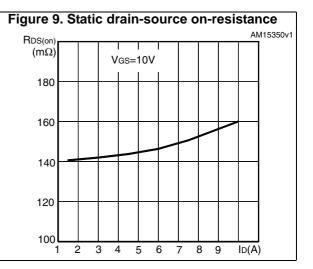
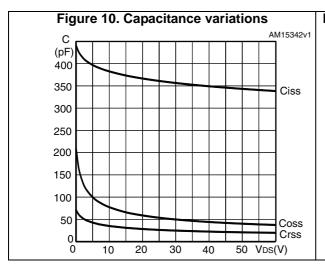
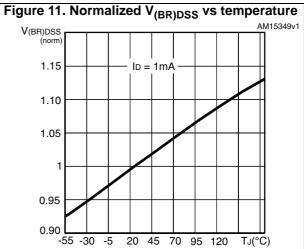


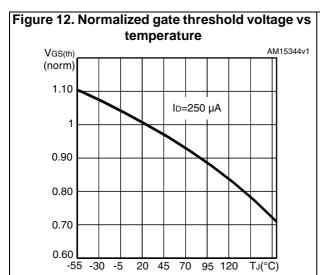
Figure 8. Gate charge vs gate-source voltage

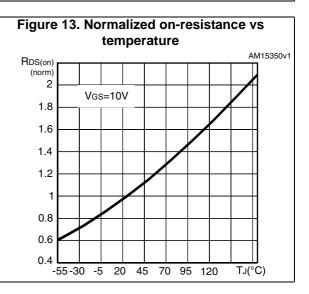
VGS
(V)
10
VDD=30V
10
10
10
10
0
2
4
6
Qg(nC)

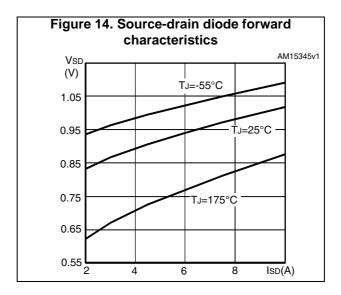












3 Test circuits

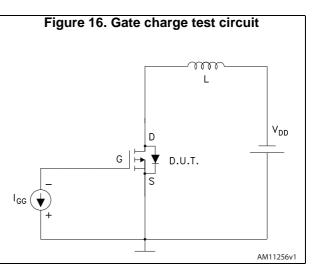
Figure 15. Switching times test circuit for resistive load

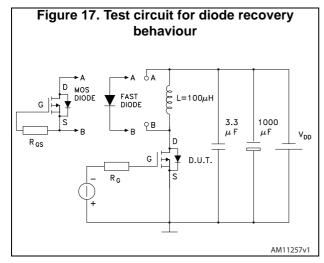
RL

VD

D.U.T.

AM11255v1





4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 DPAK package information

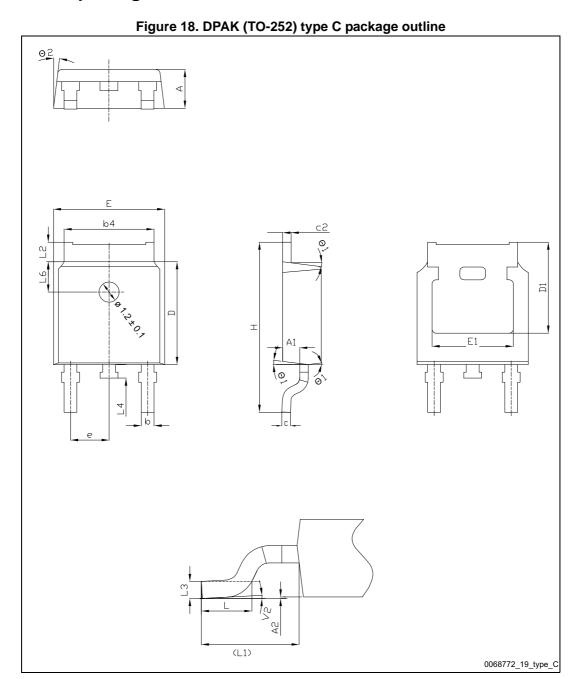


Table 8. DPAK (TO-252) type C package mechanical data

Dim.		mm		
Dim.	Min.	Тур.	Max.	
А	2.20	2.30	2.38	
A1	0.90	1.01	1.10	
A2	0.00		0.10	
b	0.72		0.85	
b4	5.13	5.33	5.46	
С	0.47		0.60	
c2	0.47		0.60	
D	6.00	6.10	6.20	
D1	5.25			
E	6.50	6.60	6.70	
е	2.186	2.286	2.386	
E1	4.70			
Н	9.80	10.10	10.40	
L	1.40	1.50	1.70	
L1		2.90 REF		
L2	0.90		1.25	
L3		0.51 BSC		
L4	0.60	0.80	1.00	
L6	1.80 BSC			
Θ1	5°	7°	9°	
Θ2	5°	7°	9°	
V2	0°		8°	

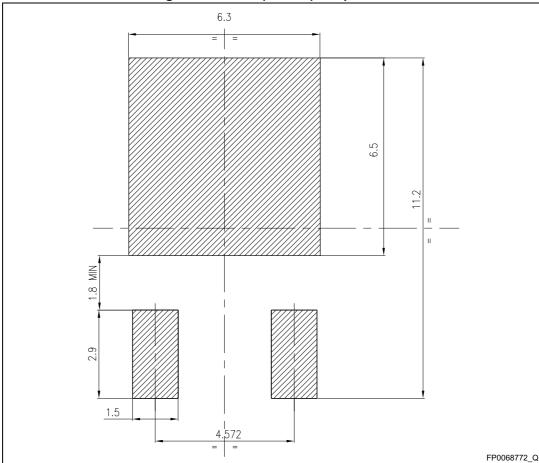


Figure 19. DPAK (TO-252) footprint (a)

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a. All dimensions are in millimeters

4.2 DPAK packing information

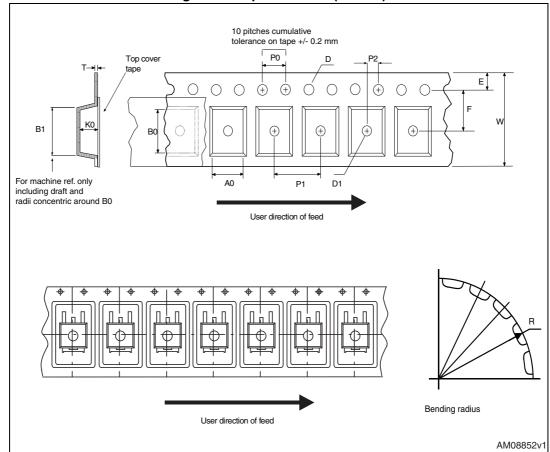


Figure 20. Tape for DPAK (TO-252)

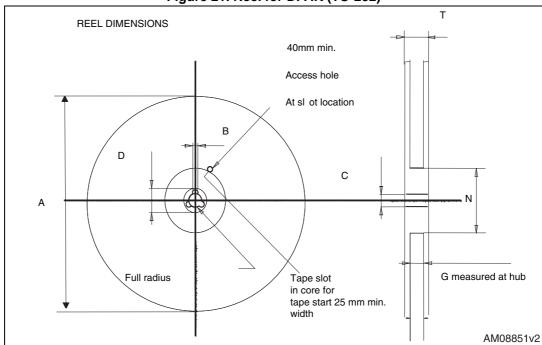


Figure 21. Reel for DPAK (TO-252)

Table 9. DPAK (TO-252) tape and reel mechanical data

	Таре			Reel		
Dim	n	nm	Dim.	mm		
Dim.	Min.	Max.	Jum.	Min.	Max.	
A0	6.8	7	Α		330	
В0	10.4	10.6	В	1.5		
B1		12.1	С	12.8	13.2	
D	1.5	1.6	D	20.2		
D1	1.5		G	16.4	18.4	
Е	1.65	1.85	N	50		
F	7.4	7.6	Т		22.4	
K0	2.55	2.75				
P0	3.9	4.1		Base qty.	2500	
P1	7.9	8.1		Bulk qty.	2500	
P2	1.9	2.1				
R	40					
T	0.25	0.35				
W	15.7	16.3				

T

4.3 TO-220FP package information

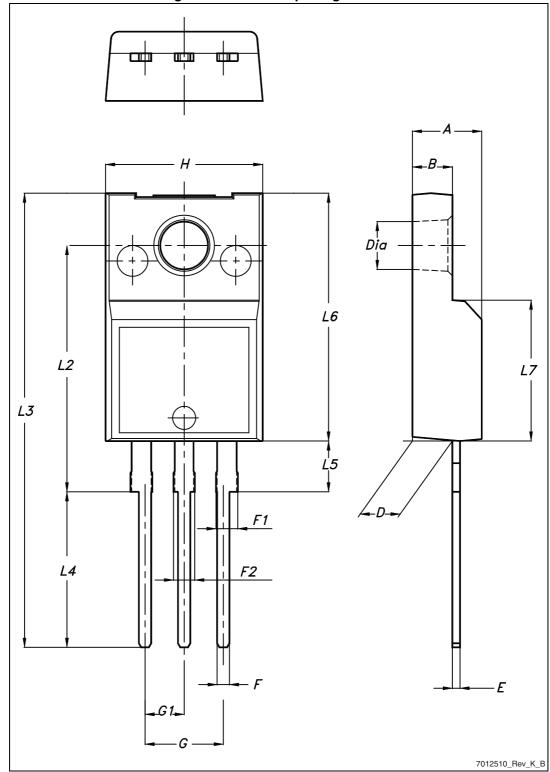


Figure 22. TO-220FP package outline

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Table 10. TO-220FP mechanical data

		mm	
Dim.	Min.	Тур.	Max.
А	4.4		4.6
В	2.5		2.7
D	2.5		2.75
Е	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
Н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

4.4 TO-220 package information

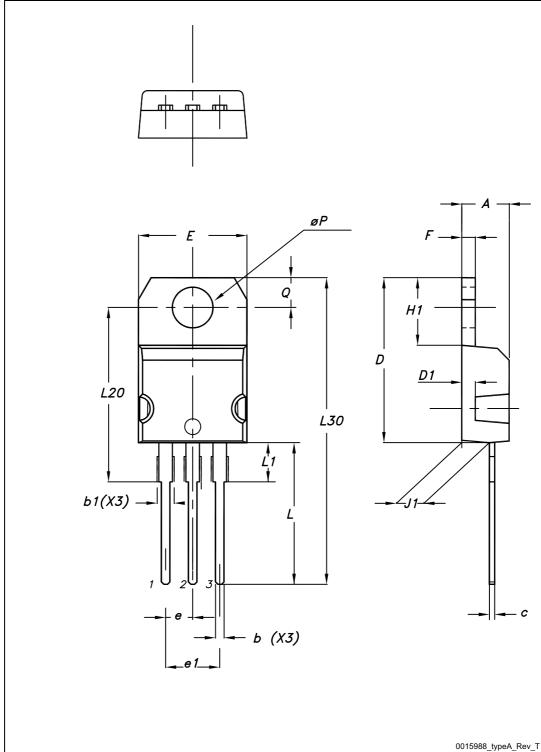


Figure 23. TO-220 type A package outline

Table 11. TO-220 type A mechanical data

Dim.	mm			
	Min.	Тур.	Max.	
А	4.40		4.60	
b	0.61		0.88	
b1	1.14		1.70	
С	0.48		0.70	
D	15.25		15.75	
D1		1.27		
Е	10		10.40	
е	2.40		2.70	
e1	4.95		5.15	
F	1.23		1.32	
H1	6.20		6.60	
J1	2.40		2.72	
L	13		14	
L1	3.50		3.93	
L20		16.40		
L30		28.90		
ØP	3.75		3.85	
Q	2.65		2.95	

4.5 IPAK package information

b2 (3x) b (3x) -*B5* e 1 0068771_L

Figure 24. IPAK (TO-251) type A package outline

Table 12. IPAK (TO-251) type A mechanical data

DIM	mm.		
DIW	min.	typ.	max.
А	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
е		2.28	
e1	4.40		4.60
Н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

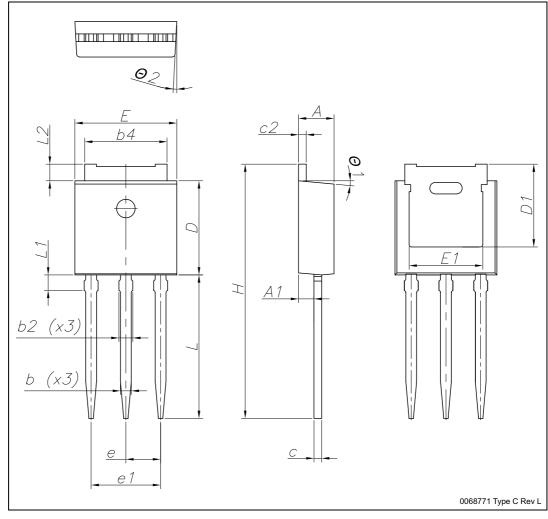


Figure 25. IPAK (TO-251) type C package outline

Table 13. IPAK (TO-251) type C mechanical data

Dim	mm			
Dim.	min.	typ.	max.	
А	2.20	2.30	2.35	
A1	0.90	1.00	1.10	
b	0.66		0.79	
b2			0.90	
b4	5.23	5.33	5.43	
С	0.46		0.59	
c2	0.46		0.59	
D	6.00	6.10	6.20	
D1	5.20	5.37	5.55	
E	6.50	6.60	6.70	
E1	4.60	4.78	4.95	
е	2.20	2.25	2.30	
e1	4.40	4.50	4.60	
Н	16.18	16.48	16.78	
L	9.00	9.30	9.60	
L1	0.80	1.00	1.20	
L2	0.90	1.08	1.25	
θ1	3°	5°	7°	
θ2	1°	3°	5°	

5 Revision history

Table 14. Document revision history

Date	Revision	Changes
10-May-2012	1	First release.
20-Jun-2012	2	Updated title on the cover page. Updated all parameter values in <i>Table 5</i> , <i>Table 6</i> and <i>Figure 1</i> .
17-May-2013	3	 Added: TO-220FP and IPAK packages Updated: R_{DS(on)} value in cover page, R_{thj-case} values, <i>Table 5</i>, 6 and 7 typical values Updated mechanical data only for DPAK in <i>Section 4: Package information</i>
24-Apr-2014	4	 Updated: Figure 2 and 3 Updated: Section 4.1: DPAK package information and Section 4.4: TO-220 package information Minor text changes
27-Jul-2015	5	 All voltage and current polarities inverted Added: note in Section 2.1: Electrical characteristics (curves) Updated: Section 4.1 and Section 4.5 Text and formatting changes throughout document



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